

150-mA Low-Noise LDO Regulator With Error Flag and Discharge Option

FEATURES

- Ultra Low Dropout—130 mV at 150-mA Load
- Low Noise—75 μ V_(rms) (10-Hz to 100-kHz Bandwidth)
- Out-of-Regulation Error Flag (power good)
- Shutdown Control
- 110- μ A Ground Current at 150-mA Load
- Fast Start-Up (50 μ s)
- 1.5% Guaranteed Output Voltage Accuracy (1.2 V, 2%)
- 300-mA Peak Output Current Capability
- Uses Low ESR Ceramic Capacitors
- Fast Line and Load Transient Response (\leq 30 μ s)
- 1- μ A Maximum Shutdown Current
- Output Current Limit
- Reverse Battery Protection
- Built-in Short Circuit and Thermal Protection

- Si91842: Output—Auto-Discharge In Shutdown Mode
- Si91844: Output—No-Discharge In Shutdown Mode
- Fixed 1.2, 1.8, 2.0, 2.2, 2.5, 2.6, 2.7, 2.8, 2.85, 2.9, 3.0, 3.3, 3.5, 3.6, 5.0-V Output Voltage Options
- SOT23-5 Package

APPLICATIONS

- Cellular Phones, Wireless Handsets
- Noise-Sensitive Electronic Systems, Laptop and Palmtop Computers
- PDAs
- Pagers
- Digital Cameras
- MP3 Player
- Wireless Modem

DESCRIPTION

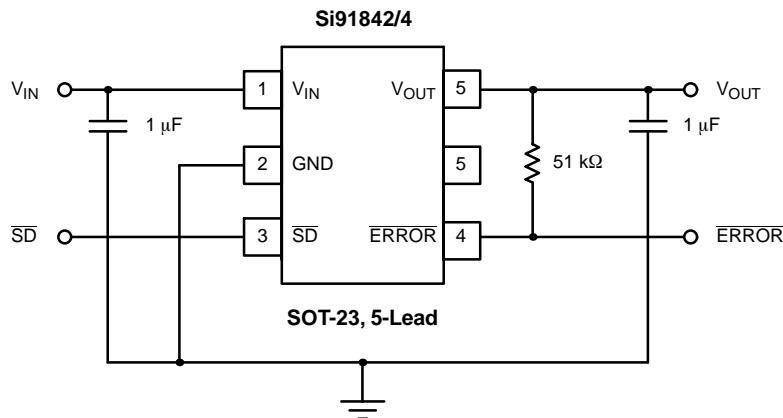
The Si91842/4 is a 150-mA CMOS LDO (low dropout) voltage regulator. It is the perfect choice for low voltage, low power applications. An ultra low ground current and ultra fast turn-on make this part attractive for battery operated power systems. The Si91842/4 also offers ultra low dropout voltage to prolong battery life in portable electronics. Systems requiring a quiet voltage source will benefit from the Si91842/4's low output noise. The Si91842/4 is designed to maintain regulation while delivering 300-mA peak current, making it ideal for systems that have a high surge current upon turn-on.

For better transient response and regulation, an active

pull-down circuit is built into the Si91842/4 to clamp the output voltage when it rises beyond normal regulation. The Si91842 automatically discharges the output voltage by connecting the output to ground through a 100- Ω n-channel MOSFET when the device is put in shutdown mode.

The Si91842/4 features reverse battery protection to limit reverse current flow to approximately 1- μ A in the event reversed battery is applied at the input, thus preventing damage to the IC.

TYPICAL APPLICATION CIRCUIT



**ABSOLUTE MAXIMUM RATINGS**

Absolute Maximum Ratings

Input Voltage, V_{IN} to GND	-6.0 to 6.5 V
V_{ERROR}, V_{SD} (See Detailed Description)	-0.3 V to V_{IN}
Output Current, I_{OUT}	Short Circuit Protected
Output Voltage, V_{OUT}	-0.3 V to $V_{IN} + 0.3$ V
Package Power Dissipation, (P_d) ^b	440 mW

Package Thermal Resistance, (θ_{JA}) ^a	180°C/W
Maximum Junction Temperature, $T_{J(max)}$	150°C
Storage Temperature, T_{STG}	-65°C to 150°C
Notes	
a.	Device mounted with all leads soldered or welded to PC board.
b.	Derate 5.5 mW/°C above $T_A = 70^\circ\text{C}$

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

RECOMMENDED OPERATING RANGE

Input Voltage, V_{IN}	2 V to 6 V	Operating Ambient Temperature, T_A	-40°C to 85°C
Input Voltage, V_{SD}	0 V to V_{IN}		

$C_{IN} = C_{OUT} = 1 \mu\text{F}$ (ceramic)

Maximum ESR of C_{OUT} : 0.4 Ω

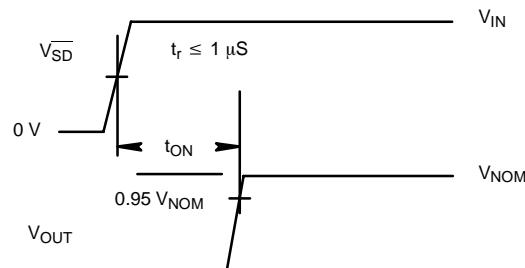
Parameter	Symbol	Test Conditions Unless Specified		Temp ^a	Limits -40 to 85°C			Unit	
		$T_A = 25^\circ\text{C}$, $V_{IN} = V_{OUT(nom)} + 1$ V, $I_{OUT} = 1$ mA, $C_{IN} = 1 \mu\text{F}$, $C_{OUT} = 1.0 \mu\text{F}$, $V_{SD} = 1.5$ V			Min ^b	Typ ^c	Max ^b		
Input Voltage Range	V_{IN}			Full	2		6	V	
Output Voltage Accuracy		$1 \text{ mA} \leq I_{OUT} \leq 150 \text{ mA}$	$V_{OUT} \geq 1.8$ V	Room	-1.5	1	1.5	% ^d	
				Full	-2.5	1	2.5		
			$V_{OUT} = 1.2$ V	Room	-2.0	1	2.0		
				Full	-3.0	1	3.0		
Line Regulation ($V_{OUT} \leq 3$ V)	$\frac{\Delta V_{OUT} \times 100}{\Delta V_{IN} \times V_{OUT(nom)}}$			Full	-0.06		0.18	%/ V	
Line Regulation (3.0 V < $V_{OUT} \leq 3.6$ V)		From $V_{IN} = V_{OUT(nom)} + 1$ V to $V_{OUT(nom)} + 2$ V		Full	0		0.3		
Line Regulation (5-V Version)		From $V_{IN} = 5.5$ V to 6 V		Full	0		0.4		
Dropout Voltage ^d , g ($V_{OUT(nom)} \geq 2.6$ V)	$V_{IN} - V_{OUT}$	$I_{OUT} = 1$ mA		Room		1		mV ^e	
		$I_{OUT} = 50$ mA		Room		45	80		
		$I_{OUT} = 150$ mA		Room		50	90		
		$I_{OUT} = 50$ mA		Full		130	180		
Dropout Voltage ^d , g ($V_{OUT(nom)} < 2.6$ V, $V_{IN} \geq 2$ V)		$I_{OUT} = 50$ mA		Room		65	100		
		$I_{OUT} = 150$ mA		Full			120		
		$I_{OUT} = 0$ mA		Room		190	250		
		$I_{OUT} = 150$ mA		Full			300		
Ground Pin Current ^e , g ($V_{OUT(nom)} \leq 3$ V)	I_{GND}	$I_{OUT} = 0$ mA		Room		100	150	μA	
		$I_{OUT} = 150$ mA		Room		110	200		
		$I_{OUT} = 0$ mA		Full			230		
Ground Pin Current ^e , g ($V_{OUT(nom)} > 3$ V)		$I_{OUT} = 150$ mA		Room		110	170		
		$I_{OUT} = 0$ mA		Full			200		
		$I_{OUT} = 150$ mA		Room		120	200		
		$I_{OUT} = 0$ mA		Full			230		
Peak Output current	$I_{O(peak)}$	$V_{OUT} \geq 0.95 \times V_{OUT(nom)}$, $t_{PW} = 2$ ms		Full	300			mA	
Output Noise Voltage	e_N	$V_{OUT} = 2.6$ V, $BW = 10$ Hz to 100 kHz, 0 mA < $I_{OUT} < 150$ mA		Room		75		$\mu\text{V(rms)}$	

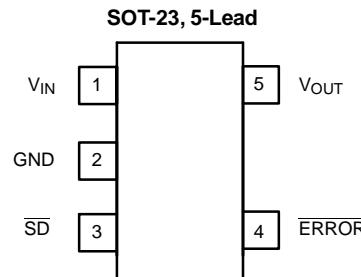
SPECIFICATIONS

Parameter	Symbol	Test Conditions Unless Specified		Temp ^a	Limits			Unit
		$T_A = 25^\circ\text{C}$, $V_{IN} = V_{OUT(\text{nom})} + 1 \text{ V}$, $I_{OUT} = 1 \text{ mA}$, $C_{IN} = 1 \mu\text{F}$, $C_{OUT} = 1.0 \mu\text{F}$, $V_{SD} = 1.5 \text{ V}$			-40 to 85°C	Min ^b	Typ ^c	
Ripple Rejection	$\Delta V_{OUT}/\Delta V_{IN}$	$I_{OUT} = 150 \text{ mA}$	$f = 1 \text{ kHz}$	Room	60			dB
			$f = 10 \text{ kHz}$	Room	40			
			$f = 100 \text{ kHz}$	Room	30			
Dynamic Line Regulation	$\Delta V_{O(\text{line})}$	$V_{IN} : V_{OUT(\text{nom})} + 1 \text{ V}$ to $V_{OUT(\text{nom})} + 2 \text{ V}$ $t_f/t_f = 2 \mu\text{s}$, $I_{OUT} = 150 \text{ mA}$	Room		20			mV
Dynamic Load Regulation	$\Delta V_{O(\text{load})}$	$I_{OUT} : 1 \text{ mA}$ to 150 mA , $t_f/t_f = 2 \mu\text{s}$	Room		25			
Thermal Shutdown Junction Temperature	$T_J(S/D)$		Room		150			°C
Thermal Hysteresis	T_{HYST}		Room		20			
Reverse current	I_R	$V_{IN} = -6.0 \text{ V}$	Room		1			μA
Short Circuit Current	I_{SC}	$V_{OUT} = 0 \text{ V}$	Room		700			mA
Shutdown								
Shutdown Supply Current	$I_{CC(\text{off})}$	$V_{SD} = 0 \text{ V}$	Room		0.1	1		μA
SD Pin Input Voltage	V_{SD}	High = Regulator ON (Rising)	Full	1.5			V_{IN}	V
		Low = Regulator OFF (Falling)	Full				0.4	
Auto Discharge Resistance	R_{DIS}	Si91842 Only	Room		100			Ω
SD Pin Input Current ^f	$I_{IN(SD)}$	$V_{SD} = 1.5 \text{ V}$, $V_{IN} = 6 \text{ V}$	Room		0.7			μA
SD Hysteresis	$V_{HYST(SD)}$		Full		150			mV
V _{OUT} Turn-On Time	t_{ON}	V_{SD} (See Figure 1), $I_{LOAD} = 100 \text{ mA}$	Room		50			μS
ERROR Output								
ERROR High Leakage	I_{OFF}	$\text{ERROR} \leq V_{IN} \cdot V_{OUT}$ in Regulation	Full			1		μA
ERROR Low Voltage	V_{OL}	$I_{SINK} = 0.5 \text{ mA}$	Full			0.4		V
ERROR Voltage Threshold	V_{ERROR}	V_{OUT} Below $V_{OUT(\text{nom})}^g$, $V_{IN} \geq 2 \text{ V}$ V_{OUT} Falling, $I_{OUT} = 1 \text{ mA}$, $V_{OUT(\text{nom})} \geq 2 \text{ V}$	Full	-2	-4	-6	%	
		$V_{OUT(\text{nom})}^g < 2 \text{ V}$, $V_{IN} > 2 \text{ V}$	Full		-4			
ERROR Voltage Threshold Hysteresis	$V_{HYST(ERROR)}$		Room		1.5			

Notes

- a. Room = 25°C , Full = -40 to 85°C .
- b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum.
- c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- d. Dropout voltage is defined as the input to output differential voltage at which the output voltage drops 2% below the output voltage measured with a 1-V differential, provided that V_{IN} does not drop below 2.0 V.
- e. Ground current is specified for normal operation as well as "drop-out" operation.
- f. The device's shutdown pin includes a typical 2-MΩ internal pull-down resistor connected to ground.
- g. $V_{OUT(\text{nom})}$ is V_{OUT} when measured with a 1-V differential to V_{IN} .

TIMING WAVEFORMS

FIGURE 1. Timing Diagram for Power-Up

PIN CONFIGURATION**PIN DESCRIPTION**

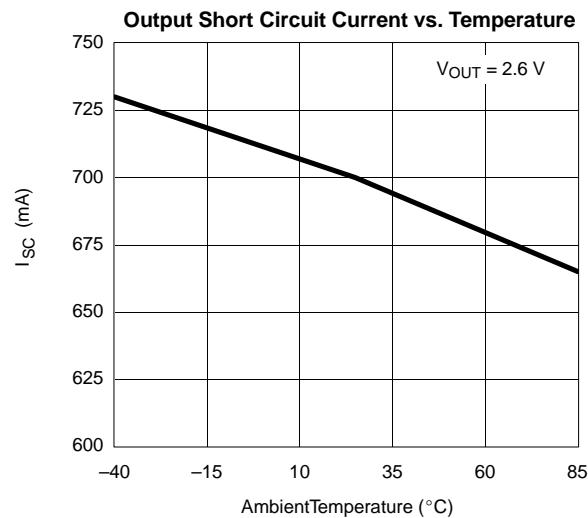
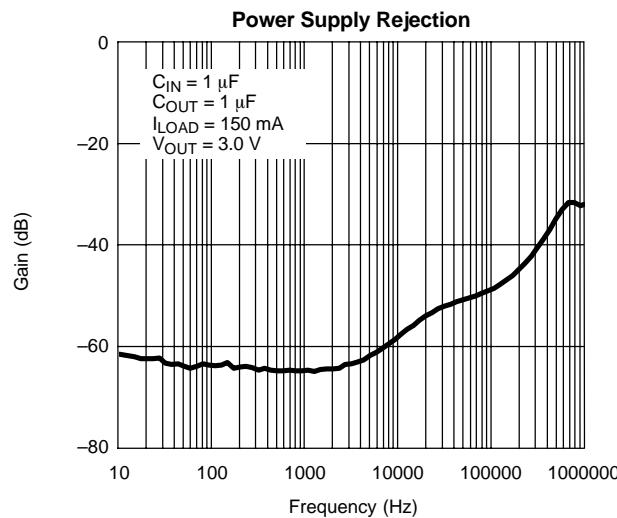
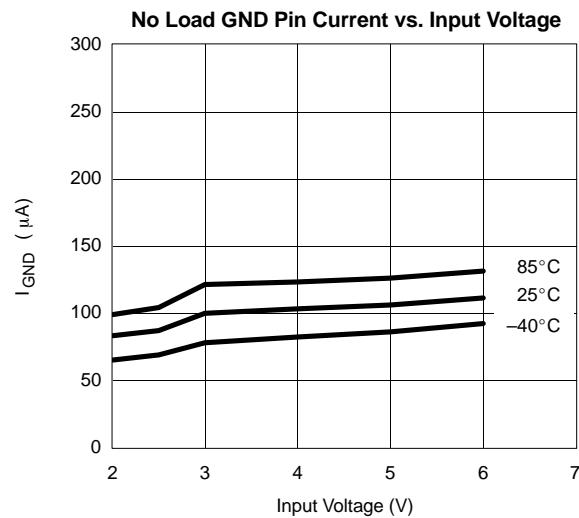
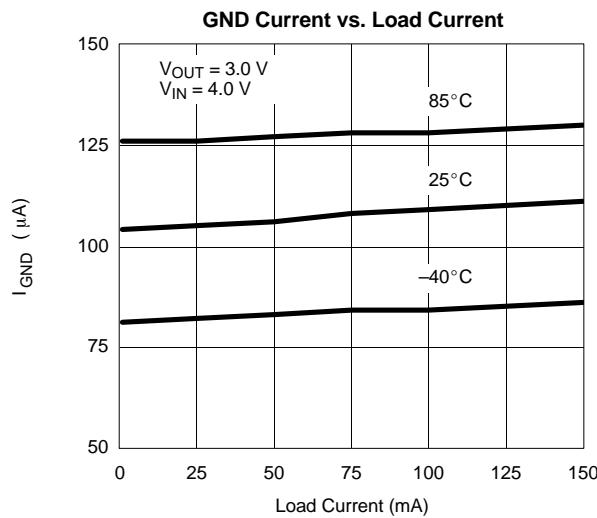
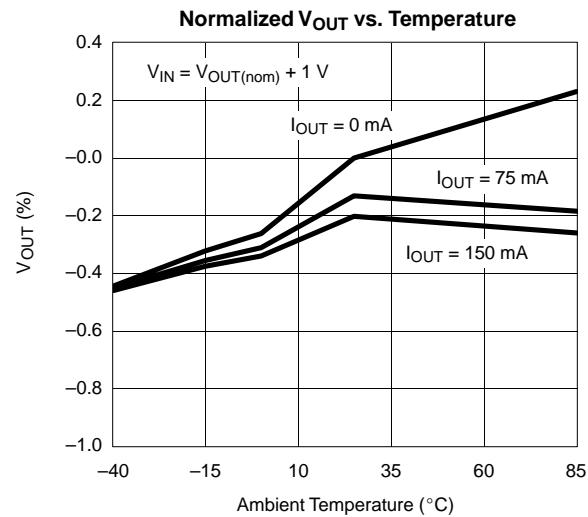
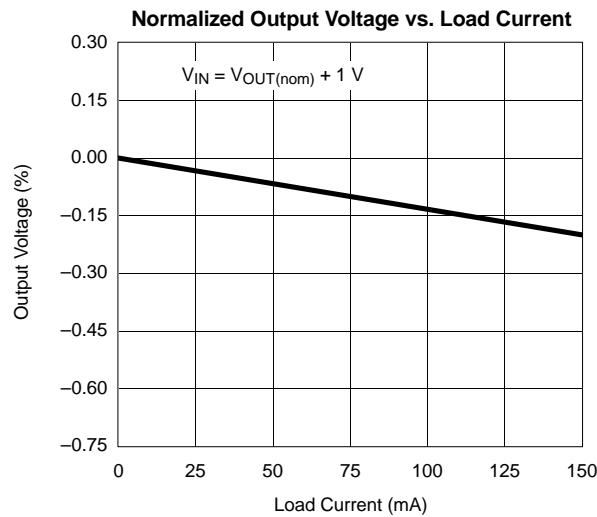
Pin Number	Name	Function
1	V _{IN}	Input supply pin. Bypass this pin with a 1- μ F ceramic or tantalum capacitor to ground
2	GND	Ground pin. For better thermal capability, directly connected to large ground plane
3	SD	By applying less than 0.4 V to this pin, the device will be turned off. Connect this pin to V _{IN} if unused
4	ERROR	The open drain output is an error flag output which goes low when V _{OUT} drops 4% below its nominal voltage.
5	V _{OUT}	Output voltage. Connect C _{OUT} between this pin and ground.

ORDERING INFORMATION

Si91842					Si91844				
Part Number	Marking	Voltage	Temp. Range	Pkg.	Part Number	Marking	Voltage	Temp. Range	Pkg.
Si91842DT-12-T1 ^b	J8LLL	1.2	-40 to 85°C	SOT23-5	Si91844DT-18-T1	F6LLL	1.8	-40 to 85°C	SOT23-5
Si91842DT-18-T1	C8LLL	1.8			Si91844DT-20-T1	F7LLL	2.0		
Si91842DT-20-T1	C9LLL	2.0			Si91844DT-22-T1	F8LLL	2.2		
Si91842DT-22-T1	C0LLL	2.2			Si91844DT-25-T1	F9LLL	2.5		
Si91842DT-25-T1	D1LLL	2.5			Si91844DT-26-T1	F0LLL	2.6		
Si91842DT-26-T1	D2LLL	2.6			Si91844DT-27-T1	G1LLL	2.7		
Si91842DT-27-T1	D3LLL	2.7			Si91844DT-28-T1	G2LLL	2.8		
Si91842DT-28-T1	D4LLL	2.8			Si91844DT-285-T1	G3LLL	2.85		
Si91842DT-285-T1	D5LLL	2.85			Si91844DT-29-T1	G4LLL	2.9		
Si91842DT-29-T1	D6LLL	2.9			Si91844DT-30-T1	G5LLL	3.0		
Si91842DT-30-T1	D7LLL	3.0			Si91844DT-33-T1	G6LLL	3.3		
Si91842DT-33-T1	D8LLL	3.3			Si91844DT-35-T1	G7LLL	3.5		
Si91842DT-35-T1	D9LLL	3.5			Si91844DT-36-T1	G8LLL	3.6		
Si91842DT-36-T1	D0LLL	3.6			Si91844DT-50-T1	G9LLL	5.0		
Si91842DT-50-T1	E1LLL	5.0							

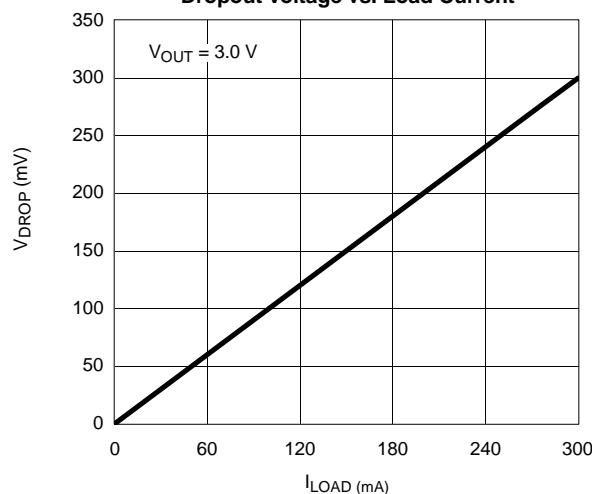
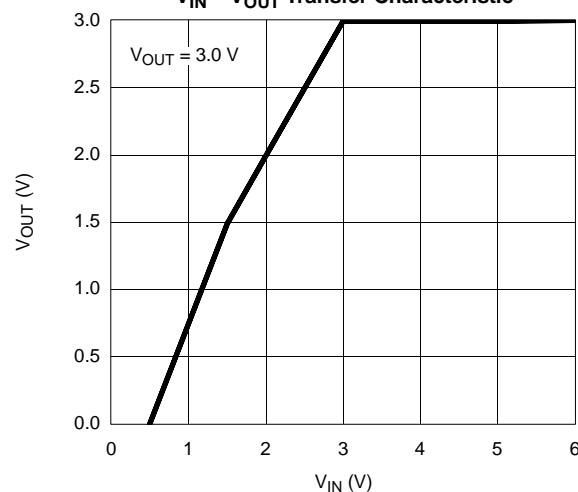
Notes:

- a. LLL = Lot Code
- b. Advanced Information, available March 2002.

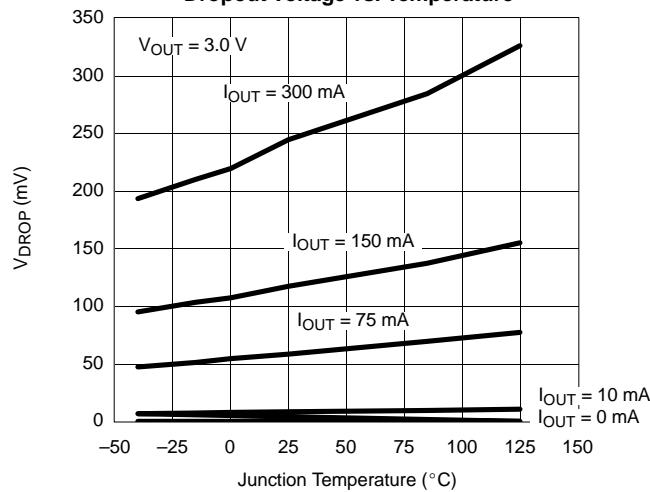
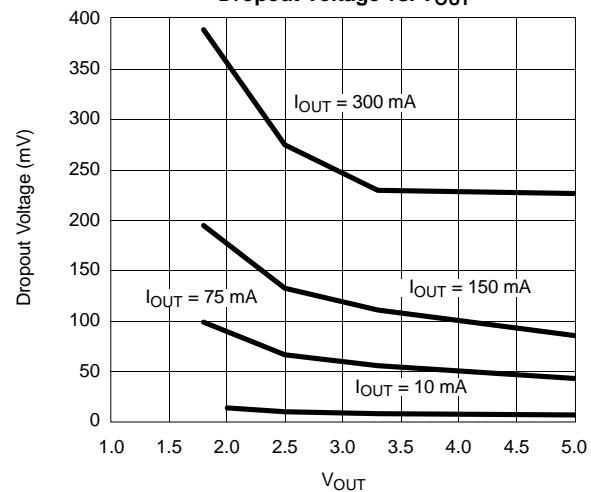
TYPICAL CHARACTERISTICS (INTERNAL REGULATED, 25°C UNLESS NOTED)


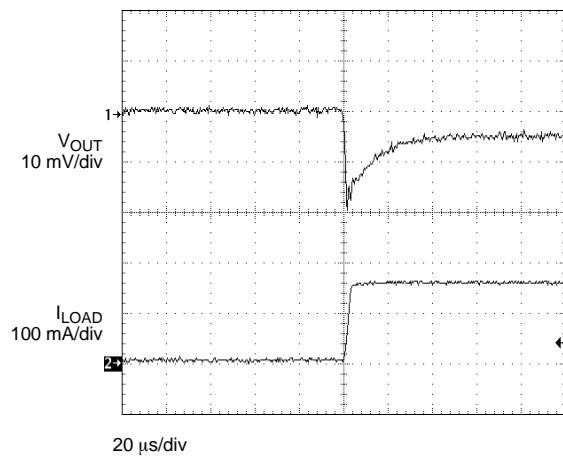
TYPICAL CHARACTERISTICS (INTERNALLY REGULATED, 25°C UNLESS NOTED)

Dropout Voltage vs. Load Current

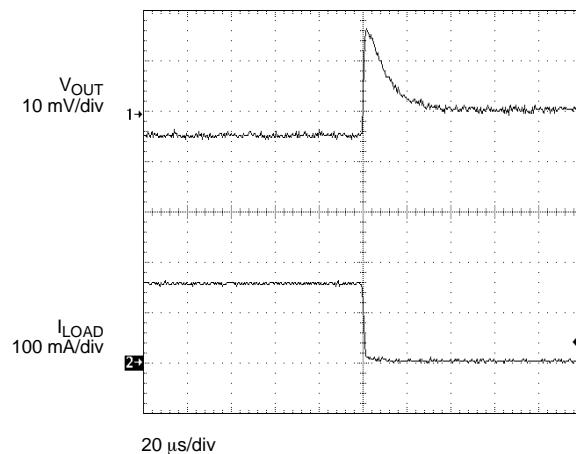
 $V_{IN} - V_{OUT}$ Transfer Characteristic

Dropout Voltage vs. Temperature

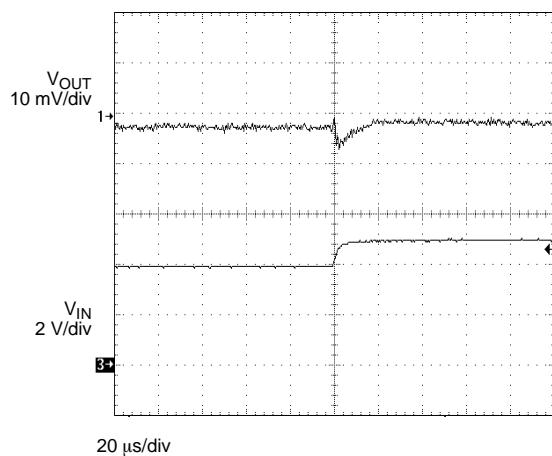
Dropout Voltage vs. V_{OUT} 

TYPICAL WAVEFORMS
Load Transient Response-1


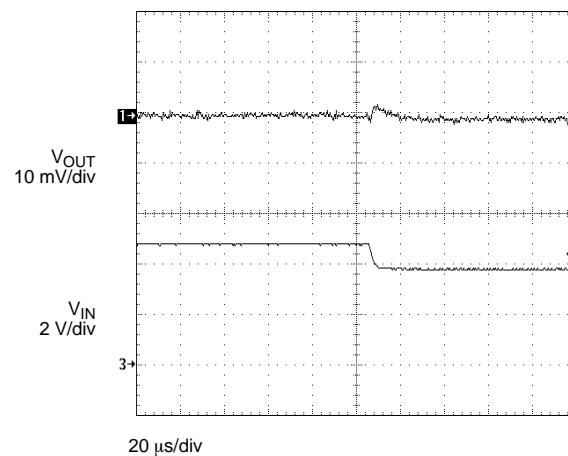
$V_{OUT} = 3.0 \text{ V}$
 $C_{OUT} = 1 \mu\text{F}$
 $I_{LOAD} = 1 \text{ to } 150 \text{ mA}$
 $t_{rise} = 2 \mu\text{sec}$

Load Transient Response-2


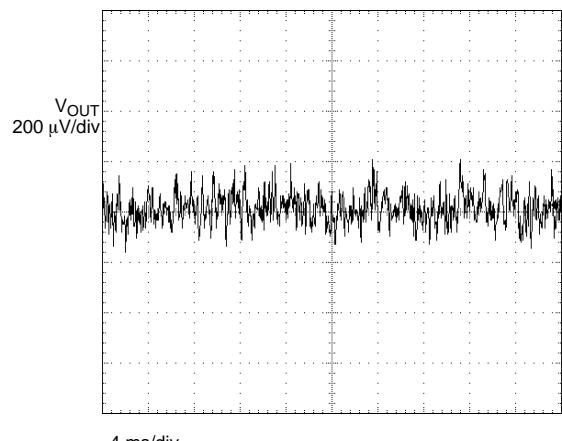
$V_{OUT} = 3.0 \text{ V}$
 $C_{OUT} = 1 \mu\text{F}$
 $I_{LOAD} = 150 \text{ to } 1 \text{ mA}$
 $t_{fall} = 2 \mu\text{sec}$

Line Transient Response-1


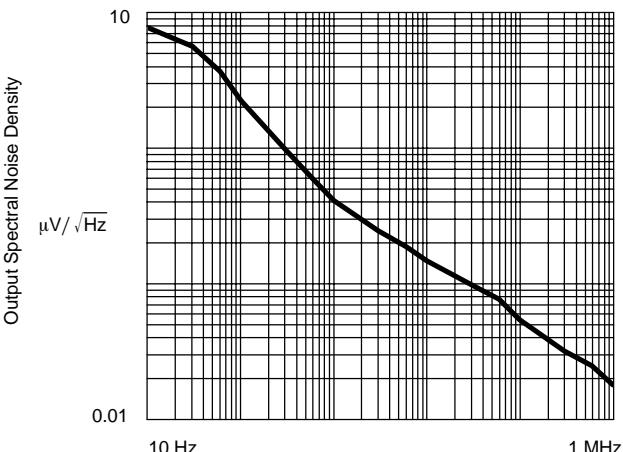
$V_{INSTEP} = 4 \text{ to } 5 \text{ V}$
 $V_{OUT} = 3 \text{ V}$
 $C_{OUT} = 1 \mu\text{F}$
 $C_{IN} = 1 \mu\text{F}$
 $I_{LOAD} = 150 \text{ mA}$
 $t_{rise} = 5 \mu\text{sec}$

Line Transient Response-2


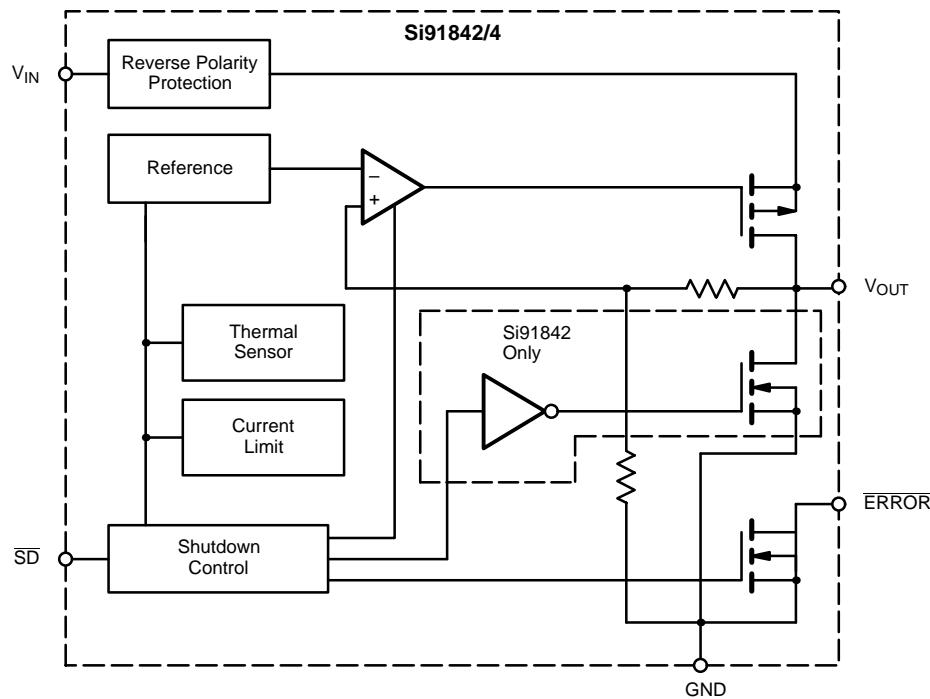
$V_{INSTEP} = 5 \text{ to } 4 \text{ V}$
 $V_{OUT} = 3 \text{ V}$
 $C_{OUT} = 1 \mu\text{F}$
 $C_{IN} = 1 \mu\text{F}$
 $I_{LOAD} = 150 \text{ mA}$
 $t_{fall} = 5 \mu\text{sec}$

TYPICAL WAVEFORMS**Output Noise**

$V_{IN} = 4 \text{ V}$
 $V_{OUT} = 3 \text{ V}$
 $I_{OUT} = 150 \text{ mA}$
BW = 10 Hz to 100 kHz

Noise Spectrum

$V_{IN} = 4 \text{ V}$
 $V_{OUT} = 3 \text{ V}$
 $I_{LOAD} = 150 \text{ mA}$

BLOCK DIAGRAM

DETAILED DESCRIPTION

The Si91842/4 is a low-noise, low drop-out and low quiescent current linear voltage regulator, packaged in a small footprint SOT23-5 package. The Si91842/4 can supply loads up to 300 mA. As shown in the block diagram, the circuit consists of a bandgap reference, error amplifier, p-channel pass transistor and feedback resistor string. Additional blocks, not shown in the block diagram, include a precise current limiter, reverse battery and current protection, and thermal sensor.

Thermal Overload Protection

The thermal overload protection limits the total power dissipation and protects the device from being damaged. When the junction temperature exceeds 150°, the device turns the p-channel pass transistor off.

Reverse Battery Protection

The Si91842/4 has a battery reverse protection circuitry that disconnects the internal circuitry when V_{IN} drops below the GND voltage. There is no current drawn in such an event. When the SD pin is hardwired to V_{IN}, the user must connect the SD pin to V_{IN} via a 100-kΩ resistor if reverse battery

protection is desired. Hardwiring the SD pin directly to the V_{IN} pin is allowed when reverse battery protection is not desired.

ERROR

ERROR is an open drain output that goes low when V_{OUT} is less than 4% of its normal value. To obtain a logic level output, connect a pull-up resistor from ERROR to V_{OUT} or any other voltage equal to or less than V_{IN}. ERROR pin is high impedance (off) when SD pin is low.

Auto-Discharge/No-Discharge

V_{OUT} has an internal 100-Ω (typ.) discharge path to ground when SD pin is low for the Si91842. the Si91844 does not have a discharge path when the SD pin is low.

Stability

The circuit is stable with only a small output capacitor equal to 6 nF/mA (= 1 μF @ 150 mA). Since the bandwidth of the error amplifier is around 1–3 MHz and the dominant pole is at the output node, the capacitor should be capacitive in this range, i.e., for 150-mA load current, an ESR <0.4 Ω is necessary. Parasitic inductance of about 10 nH can be tolerated.